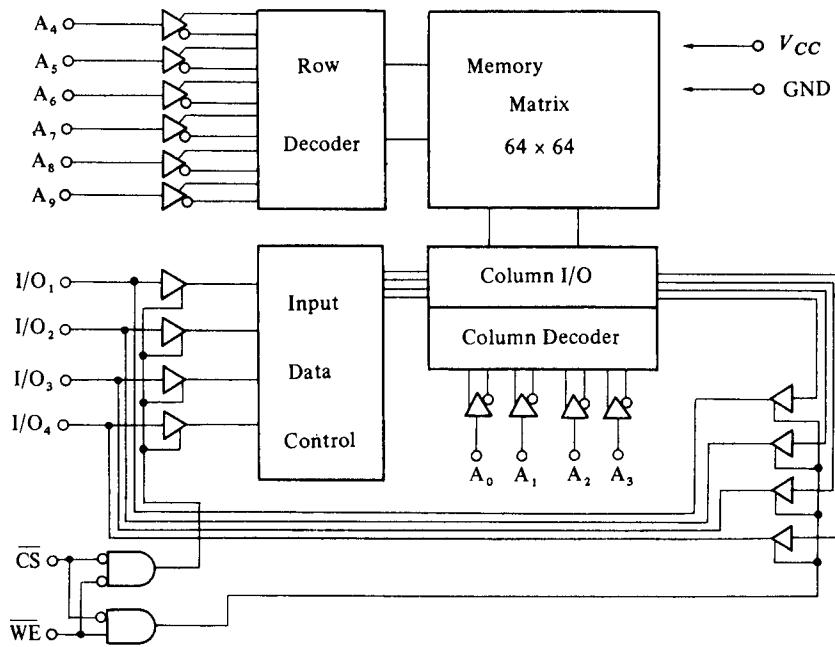


HM472114A-1, HM472114A-2, HM472114AP-1, HM472114AP-2

1024-word × 4-bit Static Random Access Memory

- Fast Access Time HM472114A-1 150ns (max.)
HM472114A-2 200ns (max.)
- Low Operating Power 200mW (typ.)
- Single +5V Supply
- Completely Static Memory No Clock or Refresh Required
- Fully TTL Compatible All Inputs and Output
- Common Data Input and Output Using Three-state Outputs
- N-channel Si Gate MOS Technology
- Pin Equivalent with Intel 2114L Series

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

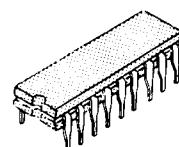
| Item | Symbol | Value | Unit |
|-------------------------------|-----------|-------------|------|
| Terminal Voltage* | V_T | -0.5 to +7 | V |
| Power Dissipation | P_T | 1.0 | W |
| Operating Temperature | T_{opr} | 0 to +70 | °C |
| Storage Temperature (Ceramic) | T_{stg} | -65 to +150 | °C |
| Storage Temperature (Plastic) | T_{stg} | -55 to +125 | °C |

* In respect to GND.

■ RECOMMENDED OPERATING CONDITIONS

| Item | Symbol | min. | typ. | max. | Unit |
|-----------------------|-----------|------|------|--------------|------|
| Supply Voltage | V_{CC} | 4.5 | 5.0 | 5.5 | V |
| Input Voltage | V_{IL} | -0.5 | — | 0.8 | V |
| | V_{IH} | 2.0 | — | $V_{CC}+1.0$ | V |
| Operating Temperature | T_{opr} | 0 | — | 70 | °C |

HM472114A-1, HM472114A-2



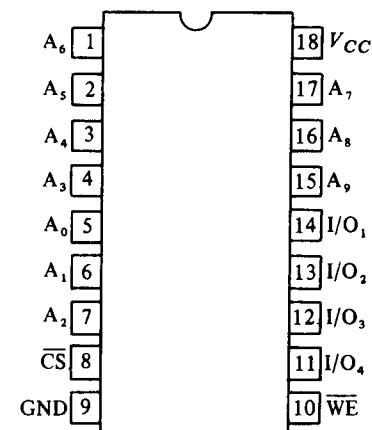
(DG-18)

HM472114AP-1, HM472114AP-2



(DP-18)

■ PIN ARRANGEMENT



(Top View)

■ DC AND OPERATING ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$, $T_a=0$ to $+70^\circ C$)

| Item | Symbol | Test Condition | min. | typ. | max. | Unit |
|-----------------------|------------|---|------|------|--------------|---------|
| Input Leakage Current | I_{LI} | $V_{in}=0 \sim 5.5V$ | — | — | 10 | μA |
| I/O Leakage Current | $ I_{LO} $ | $\overline{CS}=2.0V$, $V_{I/O}=0.4V \sim V_{CC}$ | — | — | 10 | μA |
| Supply Current | I_{CC} | $V_{in}=5.5V$, $I_{I/O}=0mA$ | — | 35 | 60* | mA |
| Input Voltage | V_{IL} | | -0.5 | — | 0.8 | V |
| | V_{IH} | | 2.0 | — | $V_{CC}+1.0$ | V |
| | V_{OL} | $I_{OL}=2.1mA$ | — | — | 0.4 | V |
| Output Voltage | V_{OH} | $I_{OH}=-0.6mA$ ($V_{CC}=4.5V$) | 2.4 | — | — | V |
| | | $I_{OH}=-1.0mA$ ($V_{CC}=4.75V$) | 2.4 | — | — | |

Note) * : in respect to HM472114A-2. This value of HM472114A-1 is 70mA.

■ CAPACITANCE ($T_a=25^\circ C$, $f=1MHz$)

| Item | Symbol | Test Condition | min. | typ. | max. | Unit |
|-------------------|-----------|----------------|------|------|------|------|
| Input Capacitance | C_{in} | $V_{in}=0V$ | — | 3 | 5 | pF |
| I/O Capacitance | $C_{I/O}$ | $V_{I/O}=0V$ | — | 5 | 7 | pF |

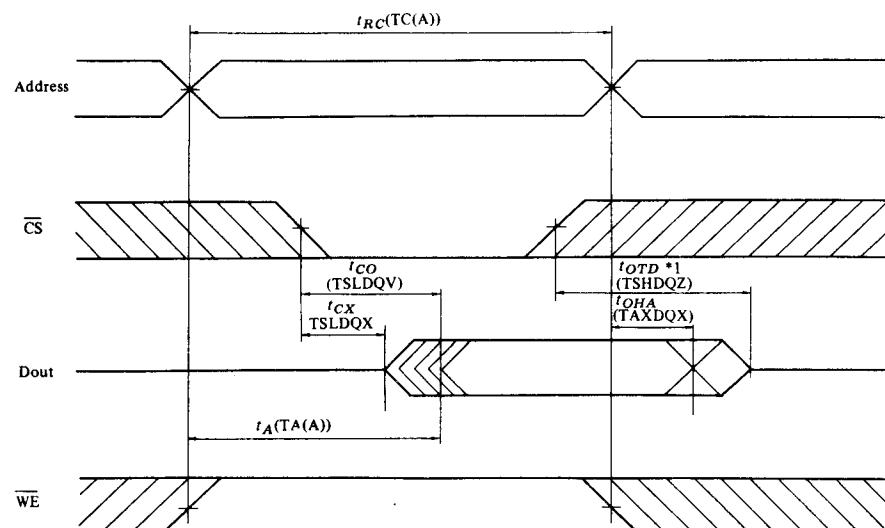
■ AC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$, $T_a=0$ to $+70^\circ C$)

• AC TEST CONDITIONS

- Input Pulse Levels 0.8V to 2.4V
- Input Rise and Fall Times 10ns
- Input and Output Timing Levels 1.5V
- Output Load 1 TTL Gate and $C_L = 100pF$

• READ CYCLE

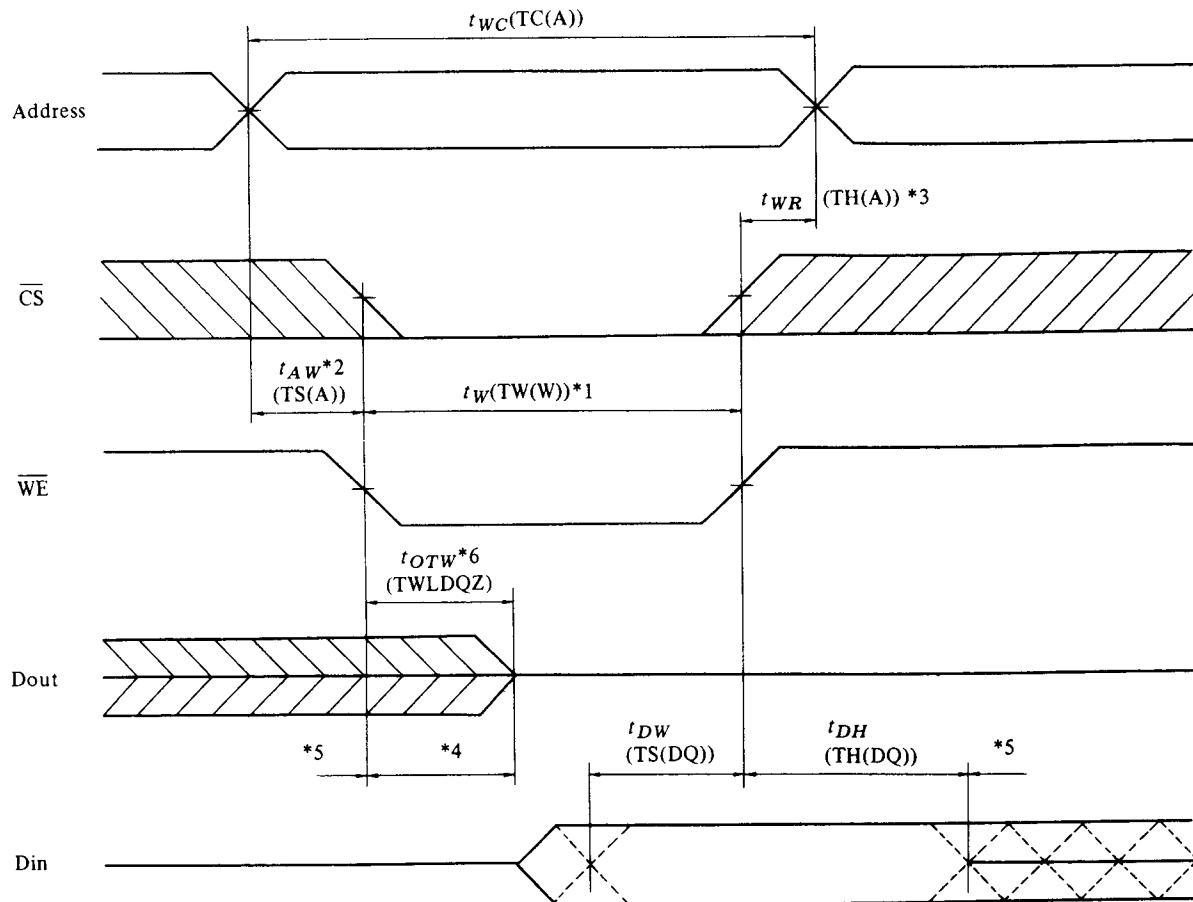
| Item | Symbol | HM472114A-1 | | HM472114A-2 | | Unit |
|----------------------------------|-----------|-------------|------|-------------|------|------|
| | | min. | max. | min. | max. | |
| Read Cycle Time | t_{RC} | 150 | — | 200 | — | ns |
| Access Time | t_A | — | 150 | — | 200 | ns |
| \overline{CS} to Output Valid | t_{CO} | — | 70 | — | 70 | ns |
| \overline{CS} to Output Active | t_{CX} | 10 | — | 10 | — | ns |
| Output 3-state from Deselection | t_{OTD} | — | 60 | — | 60 | ns |
| Output Hold from Address Change | t_{OHA} | 20 | — | 50 | — | ns |



NOTE: 1) t_{OTD} defines the time at which the outputs achieve the open circuit condition and is not referenced to output voltage levels.

• WRITE CYCLE

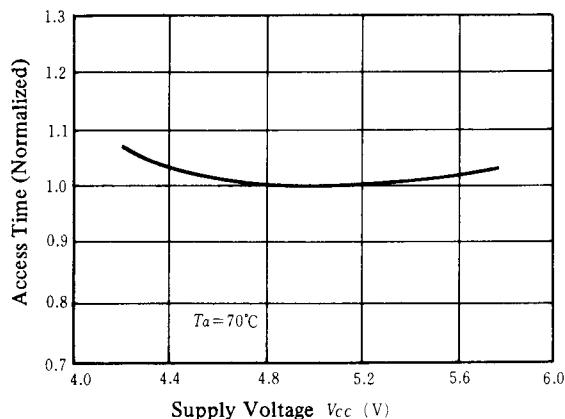
| Item | Symbol | HM472114A-1 | | HM472114A-2 | | Unit |
|-----------------------------|-----------|-------------|------|-------------|------|------|
| | | min. | max. | min. | max. | |
| Write Cycle Time | t_{WC} | 150 | — | 200 | — | ns |
| Address to Write Setup Time | t_{AW} | 20 | — | 20 | — | ns |
| Write Pulse Width | t_W | 120 | — | 120 | — | ns |
| Write Release Time | t_{WR} | 0 | — | 0 | — | ns |
| Output 3-state from Write | t_{OTW} | — | 60 | — | 60 | ns |
| Data to Write Time Overlap | t_{DW} | 70 | — | 120 | — | ns |
| Data Hold from Write Time | t_{DH} | 0 | — | 0 | — | ns |



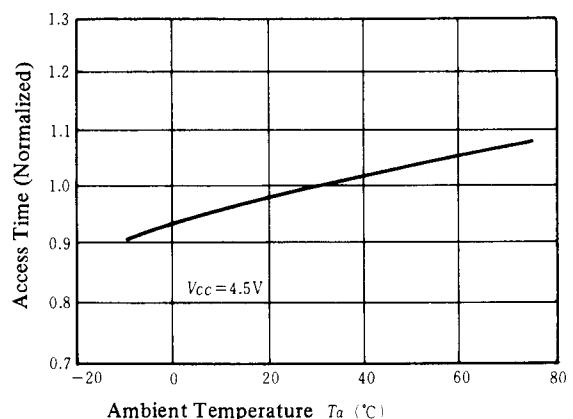
NOTE:

- 1) A Write occurs during the overlap of a low \overline{CS} and a low \overline{WE} (t_W).
- 2) t_{AW} is measured from the address setting to the latter of \overline{CS} or \overline{WE} going low.
- 3) t_{WR} is measured from the earlier of \overline{CS} or \overline{WE} going high to the end of the write cycle.
- 4) During this period I/O pins are in the output state, so that the input signals of opposite phase to the outputs must not be applied to them.
- 5) If \overline{CS} is low during this period, I/O pins are in the output state. Then the input signals of opposite phase to the outputs must not be applied to them.
- 6) t_{OTW} defines the time at which the outputs achieve the open circuit condition and is not referenced to output voltage levels.

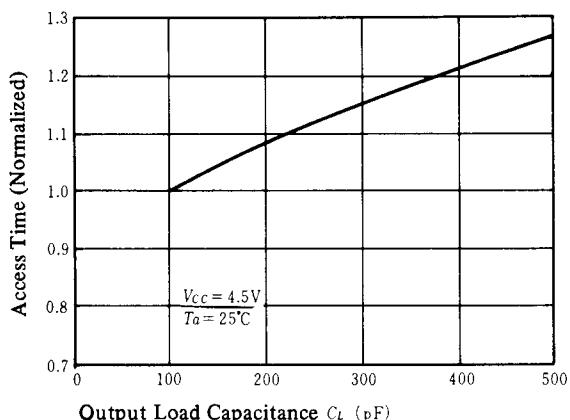
ACCESS TIME vs. SUPPLY VOLTAGE



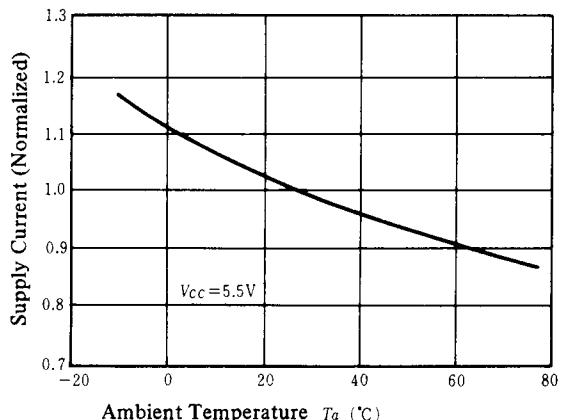
ACCESS TIME vs. AMBIENT TEMPERATURE



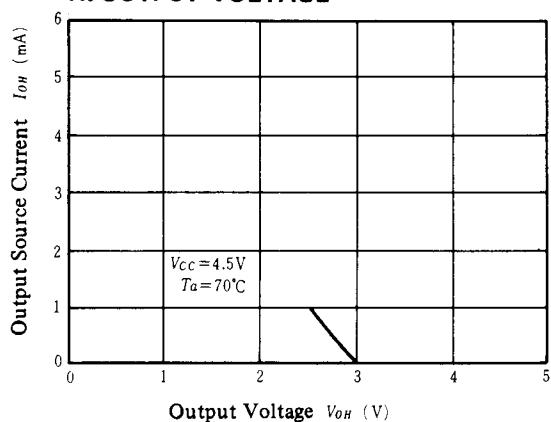
**ACCESS TIME
vs. OUTPUT LOAD CAPACITANCE**



**SUPPLY CURRENT
vs. AMBIENT TEMPERATURE**



**OUTPUT SOURCE CURRENT
vs. OUTPUT VOLTAGE**



**OUTPUT SINK CURRENT
vs. OUTPUT VOLTAGE**

